US-PAT-NO: **6115292**

DOCUMENT-IDENTIFIER: US 6115292 A

TITLE: Memory configuration of a composite memory device

DATE-ISSUED: September 5, 2000

US-CL-CURRENT: 365/185.33, 365/185.29 , 365/189.04 , 365/218

APPL-NO: 09/ 080696

DATE FILED: May 18, 1998

FOREIGN-APPL-PRIORITY-DATA:

COUNTRY	APPL-NO	APPL-DATE
JP	9-149975	May 23, 1997

———— KWIC ————

US Patent No. - PN (1):
  6115292

Application Filing Year - AY (1):
  1998

Brief Summary Text - BSTX (21):
  According to another aspect of the present invention, a composite flash memory device according to claim 1, further includes a selector selecting an single sector erasing mode which the sectors of the flash memory device are erased by a sector unit and a simultaneously plural sector erasing mode that simultaneously erases the sectors of a regular range in the plural sector flash memory device.

Detailed Description Text - DETX (13):
  In this embodiment, the composite flash memory device 100 is capable of erasing the only one sector comprised of 128-byte unit, also erasing one block comprised of 8 K byte unit (64 sectors) and furthermore, erasing certain range of plural 8 K byte unit.

Detailed Description Text - DETX (15):
  Now referring to FIG. 4, a selector circuit 39 is located in the composite flash memory device 100 and can select two erasing modes. One mode is a single erasing mode that selected only one sector of the flash memory 12B is erased. The other mode is a block unit erasing mode that the selected single block or

plural block corresponding to the selected range of the <u>flash</u> memory 12B is <u>erased</u>.

Claims Text - CLTX (7):

a selector for selecting a single <u>sector erasing</u> mode in which the <u>sectors</u> of the first <u>flash</u> memory array are <u>erased by a sector unit and a simultaneously plural sector erasing mode that simultaneously erases the sectors</u> of a regular range in the first <u>flash</u> memory array.

Claims Text - CLTX (14):

selector means for selecting a single <u>sector erasing</u> mode in which the <u>sectors</u> of said first <u>flash</u> memory means are <u>erased by a sector unit and a simultaneously plural sector erasing mode that simultaneously erases the sectors</u> of a regular range in the first <u>flash</u> memory means.